

Description

The SX3N100D is silicon N-channel Enhanced VDMOSFETs, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency.

General Features

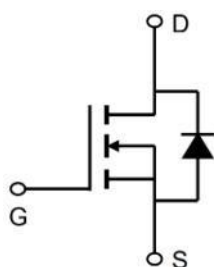
$V_{DS} = 1000V$ $I_D = 3.0A$

$R_{DS(ON)} < 5500m\Omega$ @ $V_{GS}=10V$

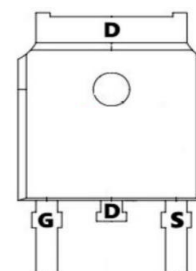
Application

Uninterruptible Power Supply(UPS)

Power Factor Correction (PFC)



TO-252-3L



Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source Voltage	1000	V
$I_D @ T_c=25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	3.0	A
$I_D @ T_c=100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	1.8	A
I_{DM}	Pulsed Drain Current	12	A
V_{GS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulse Avalanche Energy	80	mJ
I_{AS}	Avalanche Current	4	A
E_{AR}	Repetitive Avalanche Energy	0.32	mJ
P_D	Power Dissipation ($T_C = 25^\circ C$)	25	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	$-55 \sim +150$	$^\circ C$
R_{thJC}	Thermal Resistance, Junction-to-Case	5	$^\circ C/W$
R_{thJA}	Thermal Resistance, Junction-to-Ambient	62.3	$^\circ C/W$

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V(BR)DSS	Drain-Source Breakdown Voltage	VGS=0V, ID=250μA	1000	1100	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=1000V, VGS=0V, T _J =25°C	--	--	1	μA
IGSS	Gate-Source Leakage	VGS = ±20V	--	--	±100	nA
VGS(th)	Gate-Source Threshold Voltage	VDS=VGS, ID= 250μA	2.0	3.5	4.0	V
RDS(on)	Drain-Source On-Resistance (Note3)	VGS=10V, ID=1.0A	--	4600	5500	mΩ
Ciss	Input Capacitance	VGS=0V, VDS=25V, f=1.0MHz	--	535	--	pF
Coss	Output Capacitance		--	53	--	
Crss	Reverse Transfer Capacitance		--	10	--	
Qg	Total Gate Charge	VDD=800V, ID=3.0A, VGS=15V	--	24	--	nC
Qgs	Gate-Source Charge		--	2.6	--	
Qgd	Gate-Drain Charge		--	14.9	--	
td(on)	Turn-on Delay Time	VDD=500V, ID=3.0A, RG=25Ω	--	36	--	ns
tr	Turn-on Rise Time		--	13	--	
td(off)	Turn-off Delay Time		--	110	--	
tf	Turn-off Fall Time		--	37	--	
IS	Continuous Body Diode Current	TC=25°C	--	--	3	A
ISM	Pulsed Diode Forward Current		--	--	12	
VSD	Body Diode Voltage	T _J =25°C, ISD=1.5A, VGS=0V	--	--	1.4	V
trr	Reverse Recovery Time	VGS=0V, IS=3.0A, diF/dt =100A /μs	--	886	--	ns
Qrr	Reverse Recovery Charge		--	0.9	--	μC

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The EAS data shows Max. rating . L=10mH IAS=5A, VDD=50V, RG=25Ω, Starting T_J=25°C
- 3、The test condition is Pulse Test: Pulse width ≤ 300μs, Duty Cycle ≤ 1%
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

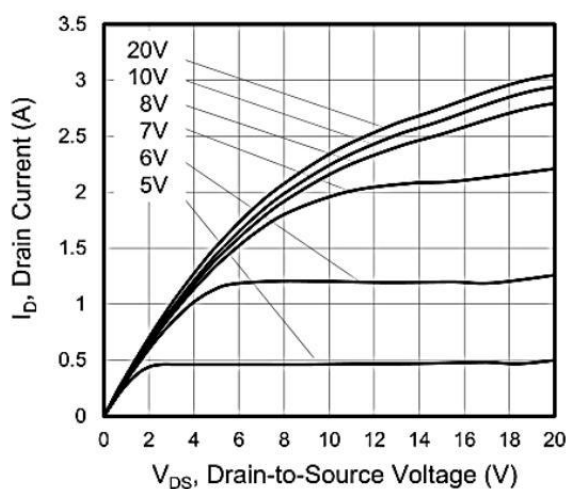


Figure 1. Output Characteristics

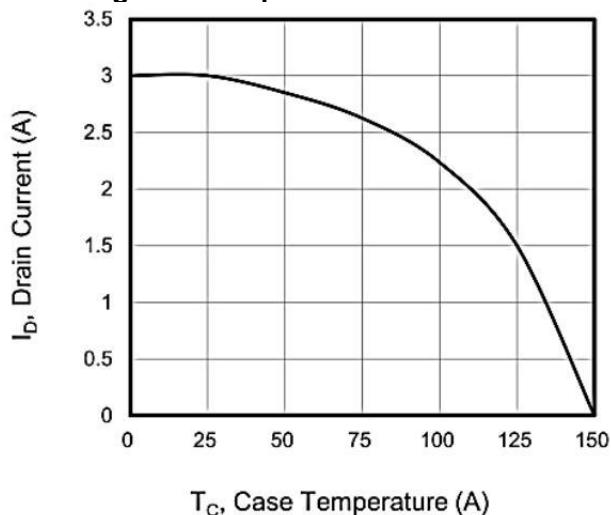


Figure3. Drain Current vs. Temperature

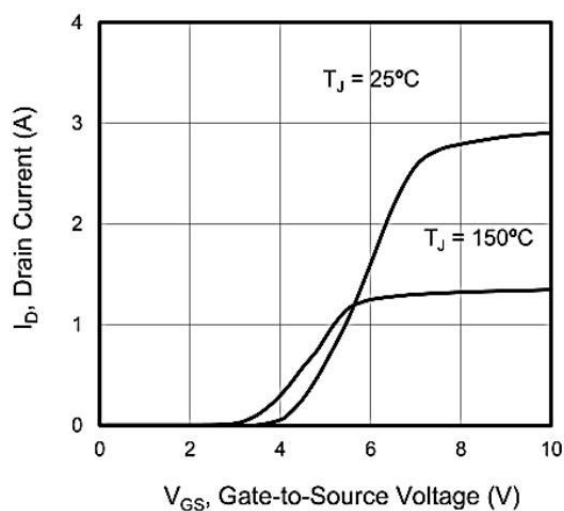


Figure 5. Transfer Characteristics

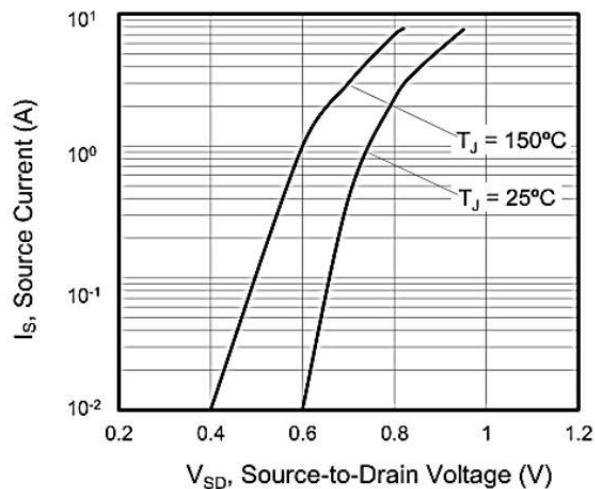


Figure 2. Body Diode Forward Voltage

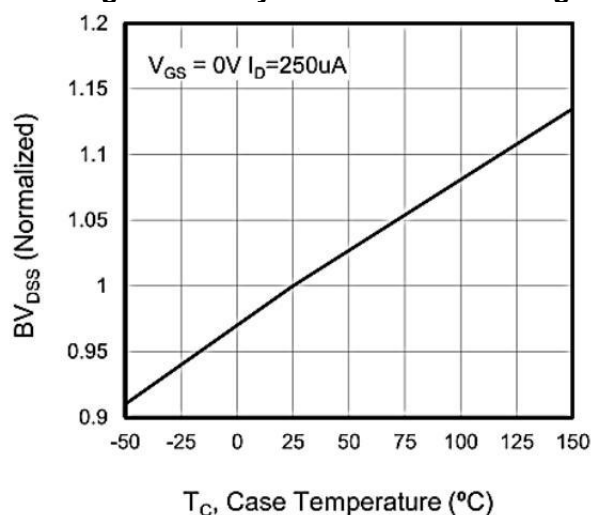


Figure4. BVDSS Variation vs. Temperature

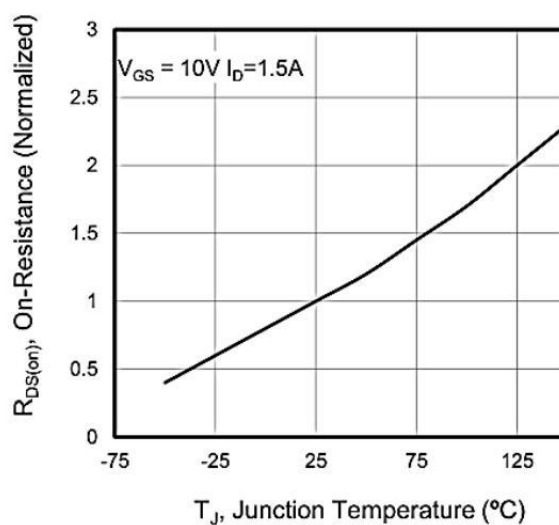


Figure 6. On-Resistance vs. Temperature

Typical Characteristics

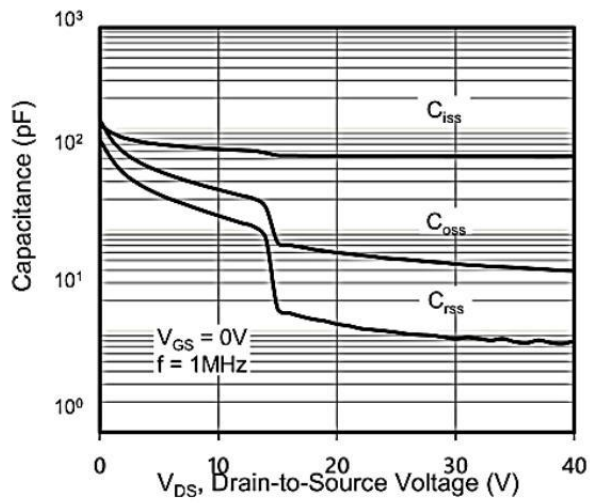


Figure 7. Capacitance

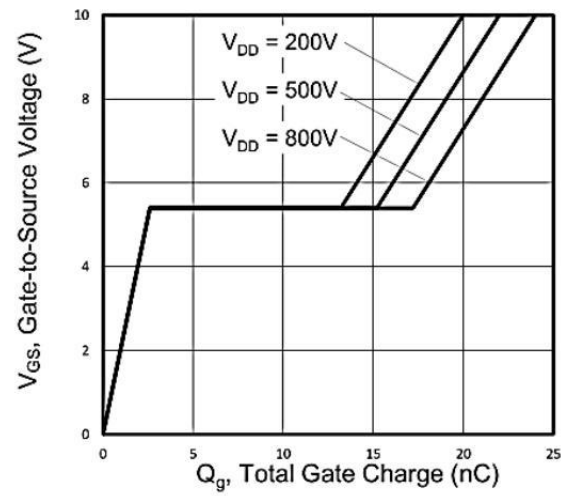


Figure 8. Gate Charge

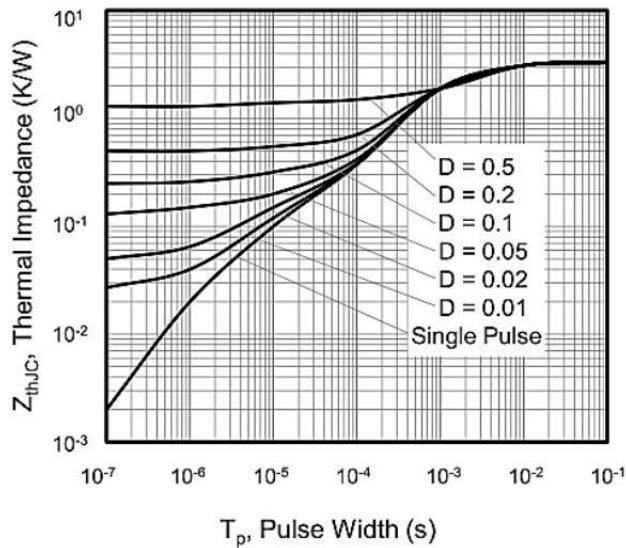
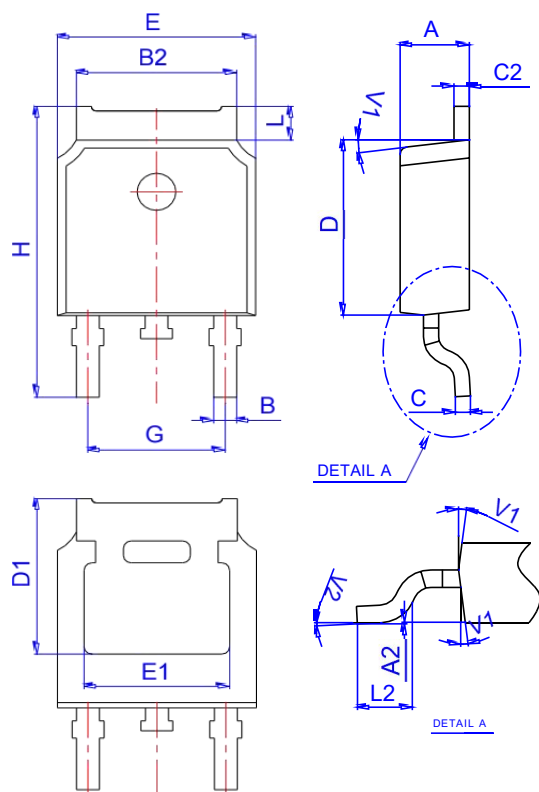


Figure 9. Transient Thermal Impedance

Package Mechanical Data: TO-252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	TO-252-3L		2500